EA/MZ Modulator Driver PMCC_EAMD12G



IP MACRO

Datasheet Rev 1.0

Process: Jazz Semiconductor SBC18HX

DESCRIPTION

The PMCC_EAMD12G is designed to directly drive the 50Ω inputs of EA or MZ Modulators or EML devices at data-rates up-to 11.3Gbps. The driver features programmable output voltage swing as well as monitoring, crossing point control, and programmable output DC offset (bias). The IP block is designed using Jazz SiGe120 (SBC18HX) process. Modulator driver features fully differential architecture. I/O signal levels, control functions and features can be customized upon special agreement.

Applications include: Electro Absorption and MZ Modulators and DFB lasers in Fiber optic communications; broadband high output swing Limiting Amplifiers from DC to 12Gb/s.

FEATURES

- Data-rates from 1.25Gb/s to 11.3Gb/s.
- Single –5.2V Power Supply
- Programmable output voltage from 1Vp-p to 3Vp-p Single ended and from 2Vp-p to 6Vp-p differential
- Programmable EAM bias voltage up to 1V
- Crossing point control
- Selectable data retiming
- 90deg at 11.3Gb/s clock phase stepping
- 25ps typical rise/fall-time
- Data polarity invert
- Output Level Monitoring
- Selectable NRZM encoding
- Power consumption: 1W

BLOCK DIAGRAM

Block diagram of the macro is shown on Figure 1. NRZ data is supplied to the inputs INP/INN. Output data is picked up from outputs OUTP/OUTN. Optional clock is applied to inputs CLKP/CLKN.

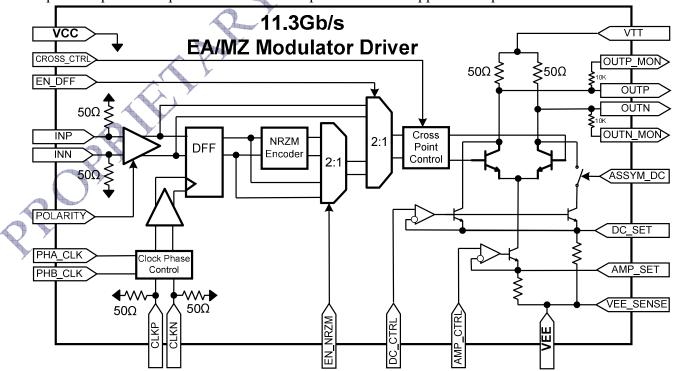


Figure 1. EA Modulator Driver IP Block Diagram

MACRO SCHEMATIC SYMBOL. PIN DESCRIPTION. Table 1 Pin Descriptions

Name	Pin #	Description	Function
AMP_CTRL	1	Control input to vary the driver output swing. Adjusts the $V_{\rm OUT\text{-}LOW}$ level with respect to $V_{\rm OUT\text{-}HIGH}$ on the OUTP and OUTN outputs.	Analog input
DC_CTRL	2	Control input to vary the DC bias of the driver output. Simultaneously adjusts $V_{\text{OUT-LOW}}$ and $V_{\text{OUT-HIGH}}$ on the OUTP and OUTN outputs.	Analog input
EN_DFF	3	Enables the retiming function. Connect to VCC to enable the retiming on incoming data. Connect to VEE to disable re-timing.	Digital input
PHA_CLK	4	Controls the phase of the clock. Connect to VCC to enable phase A. Connect to VEE to disable. Look at the truth table of the clock phase select for more details.	Digital input
PHB_CLK	5	Controls the phase of the clock. Connect to VCC to enable phase B. Connect to VEE to disable. Look at the truth table of the clock phase select for more details.	Digital input
CROSS_CTRL	6	Controls the cross point of the output data eye. Increasing of the voltage shifts up the crossing point of the output data eye on direct output. Look at the graphs for more information.	Analog input
VEE_SENSE	7,10, 21	The output is provided for the loopback of control signals. Using of the pin instead of the global ground helps to avoid unwanted ground bounce effects.	VEE
AMP_SET	8	Sets the initial amplitude of OUTP and OUTN outputs. Connect via $1.8~\Omega$ resistor to VEE_SENSE. See application schematic for details.	Analog input
EN_NRZM	9	Enables Non-Return-to-Zero-Mark encoding. This function is used as part of optical duo binary encoding. Connect to VCC to enable or to VEE to disable.	Digital input
VCC	11,13, 14,16, 22,24, 26,30, 32,34	Connect to ground if negative power supply is used (preferred). Connect to VCC if positive power supply is used.	Power supply
OUTP OUTN	12/15	High-speed differential driver outputs. On-chip 50Ω termination to VTT provided. Each output must be coupled to a 50Ω load. No DC block is allowed.	High speed CML output
VTT	17	Back Termination for OUTP and OUTN outputs. This pin should be decoupled to ground. See application schematic for details.	Analog
OUTN_MON OUTP_MON	18/19	Driver output level monitor ports. Connected to the OUTP and OUTN outputs via internal $10 \text{K}\Omega$ resistors. Connect to VCC or leave open if not used.	Analog output
DC_SET	20	Sets the initial DC bias level for the OUTP and OUTN outputs.	Analog input

		Connect via 2.7Ω resistor to VEE_SENSE. See application schematic for details.	
CLKP CLKN	25/23	High-speed differential clock inputs. On-chip 50Ω termination to VCC provided. Each output must be coupled to a 50Ω load. DC blocking capacitor is needed. See application schematic for details.	High speed Analog input
POLARITY	27	Data output logic invert. - LOW (or leave open) for normal logic. - HIGH to invert OUTP and OUTN logic.	Digital input
VEE	28,35	Power supply input. Connect to filtered –5.2V supply. See application schematic for regulation and filter recommendations. Connect to ground if positive power supply is used.	Power supply
ASYMM_DC	29	Enables asymmetric DC biasing of the differential output. - LOW (or leave open) for normal biasing - HIGH to remove biasing from OUTN	Digital input
INP INN	31/33	High-speed data differential input. On-chip 50Ω termination to VCC is provided. Each output must be coupled to a 50Ω load. Either DC or AC coupling is allowed.	High speed CML output
CB_MON	36	A monitoring pin for design validation purposes. Must be left open.	Analog output

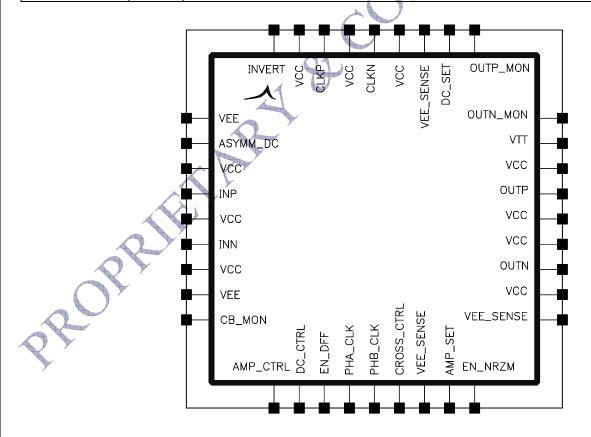


Figure 2. Macro schematic symbol

Table 2. Electrical absolute maximum ratings

Description	Min	Max	Units
Power supply (pin VEE)	-6		V
Control input voltage	-6	+0.5	V
Junction temperature	-25	125	°C
End Of Life (EOL)	10		years

DC Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Table 3. DC Electrical Specifications

Parameter			Min	Тур	Max	Units	Notes
Power Supply (VEE)			-5.46	-5.2	-4.95	V	
Power With Retin		etiming Option		0.23		A	$V_{DC} = 1V, V_{SW} = 2V$
Supply Current	Without Retiming Option			0.22		A	$V_{DC} = 1V, V_{SW} = 2V$
Current	With Retiming Option and 0V DC offset			0.2		A	$V_{DC} = 0V, V_{SW} = 3V$
	on Resis	tance at the Input	43	50	59	Ω	Limits for process variation
(SE)							over $\pm 3\sigma$
Bias Volta	age Cont	rol Range	0		1	V	Photocurrent from
					y .		modulator is not accounted
							for
Swing Co	ntrol Raı	nge	0.75		3	V	Photocurrent from
			01	à			Modulator is not taken into
				•			account
Bias Settin	ng Resist	tor		2.7		Ω	External
Swing Set	ting Res	istor		1.8		Ω	External
Bias Cont	Bias Control Voltage (DC CTRL)				VEE+2	V	
Swing Control Voltage			VEE		VEE+2	V	
(SWING_CTRL)							
Digital	-	Logic High	-1		0	V	
Control Input Logic Low			VEE		VEE+1	V	Left open sets logic Low
Voltages	•						

Table 4 AC Electrical Specifications

I/O Port	Parameter	Symbol	Min.	Тур.	Max.	Units
Q*	Data rate	f_b	0.155	10	11.3	Gb/s
7	Programmable Amplitude Range Single-ended measured into 50Ω , DC offset = 0V, controlled via AMP_ADJ	V _{OUT}	1.0		3.0	Vpp
	High Level varied via DC_ADJ input	V _{OUT-HIGH}	-1.0		0	V
	Low Level varied via DC_ADJ & AMP_ADJ	V _{OUT-LOW}	-3.0		-1.0	V
	Rise / Fall Time Measured at 20% - 80% voltage levels.	t_r, t_f		25	35	ps

I/O Port	Parameter	Symbol	Min.	Тур.	Max.	Units	
	Crossing Point Contro varied via CPC input	CPC	20		80	%	
	Impedance Terminated to VTT	R_{DOUT}		50		Ω	
	Return Loss	50MHz – 10GHz	S ₂₂			-10	dB
Clock inputs	Clock frequency		F _{CLKO}	0.155	10	11.3	GHz
CLKP	Amplitude Single-ended measured in	Amplitude Single-ended measured into 50Ω.			500	1000	$\mathrm{mV}_{\mathrm{pp}}$
CLKN	Impedance Terminated to VCC.			50		Ω	
	Return Loss	S ₁₁			10	dB	
Data inputs	Parameter	Symbol	Min.	Тур	Max.	Units	
	Data rate		f_b	0.155	10	11.3	Gb/s
INP INN	Impedance Terminated to VCC	R_{DIN}		50		Ω	
	Return Loss	S11		人人	-10	dB	
	Input amplitude	Retiming mode	V_{DR}	30		1500	mV_{p-p}
	(single-ended)	LA mode	V_D	50		1000	mV_{p-p}

IP BLOCK TEST STRUCTURE

Test structure consisting of PMCC_EAMD12G macro mapped to a wire bond pad ring is available to make possible to tape-out a test chip for macro evaluation. Simulation schematic for the test structure is shown on Figure 3. Test IC layout presented on Figure 4.

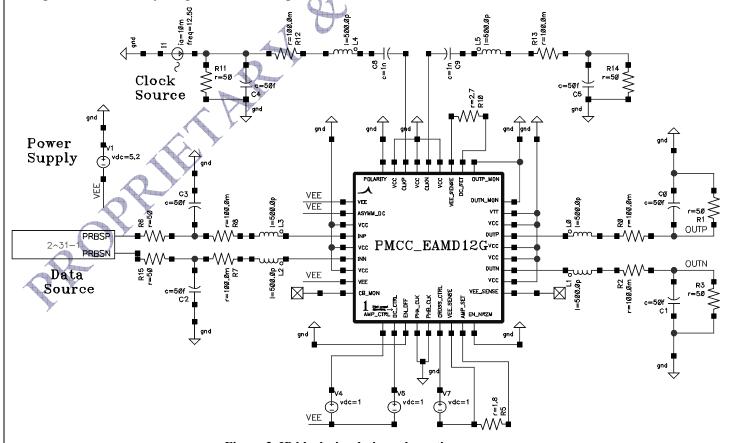


Figure 3. IP block simulation schematic

MACRO LAYOUT VIEW

PMCC_EAMD12G macro layout is optimally designed taking symmetry, parasitic capacitances, inductance and reliability into account. Layout design leverages all 6 metal layers available in the SBC18HX process. Compact layout ensures minimum parasitic capacitance, inductance, device mismatch and minimum die area.

Layout considerations for macro integration:

- METAL6 is used for ground connections to minimize "ground bounce" effects.
- METAL5 is used for VCC connection
- Transmission line structures should be considered for long interconnections in case of macro direct connection to IC pads (through optional 50 Ohm terminated input buffers)
- Other layout features incorporated by customer into or adjacent to macro can affect macro performance and should be carefully analyzed.

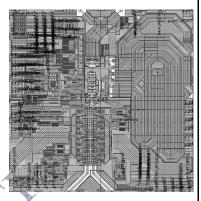


Figure 4. PMCC_EAMD12G macro core layout view. Note: some of the details and/or layers might be omitted. Layout size is 1270um x 1290um.

Table 5 Version Control

Revision	Date	Author	Changes
V1.0	06/18/09	PMCC	Initial version of the document